# Advances in Investigations of clean Nb surfaces

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- Motivation
- Enhanced field emission of Nb surfaces
- Preparation and measurement techniques
- Statistical distribution of field emitters
- FE properties and nature of emitters
- Conclusions and outlook





### **Motivation**

Accelerating fields E<sub>acc</sub> in SC Nb cavities are limited by NC defects and protrusions and surface impurities
 U

**local quenches** electron loading due to field emission

- Improved Nb purity and surface preparation techniques are required to achieve E<sub>acc</sub>>25 MV/m at Q<sub>0</sub>>10<sup>10</sup> reliably
- Advanced surface investigation of clean Nb samples by profilometry, scanning FE microscopy and SEM/EDX

**Identification of relevant features for field limitation** 

Systematic improvement and control of surface quality





### Field emission of electrons from flat metal surfaces

Electron waves of bound states in a metal can tunnel through the potential barrier V(z) at the solid surface into vacuum by means of the quantum mechanical tunnelling effect



Calculation of the current density j(E) within the Fowler-Nordheim theory results in

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$$j(E) = \frac{AE^2}{\Phi t^2(y)} \exp\left(-\frac{B\Phi^{3/2}v(y)}{E}\right)$$

with constants A=154 and B=6830 and slight correction functions t(y) and v(y)

 $\Phi$ =4eV at E=2000 MV/m  $\Rightarrow$  j= 1nA/µm<sup>2</sup>



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### **Enhanced field emission of electrons from real surfaces**

For real metal surfaces, i.e. broad area cathodes with some roughness and pollution, nA currents occur at much lower fields (<100 MV/m) than predicted by FN theory

modified FN theory with **field enhancement factor**  $\beta$  describes at least the slope of locally measured I(E) curves quite well:

$$I(E) = S \frac{A(\beta \cdot E)^2}{\Phi} \exp\left(-\frac{B\Phi^{3/2}}{\beta \cdot E}\right)$$

with emitting surface S as fit parameter

Theoretical models for enhanced field emission of real surfaces:

Geometric field enhancement for metallic protrusions/rough particulates



of height h and edge radius  $r_k \Rightarrow \beta \approx h/r_k$ 

- Metal-Isolator-Vacuum for metals with oxide layers (d < 10 nm)
   ⇒ irreversible creation of conducting channels ⇒ switch-on effect</li>
- Antenna or Metal-Isolator-Metal for particles on oxidized metals

after switch-on at  $\beta \approx h/d$  geometric field enhancement as above

• Resonant tunneling through localized states in adsorbates and oxides

 $\Rightarrow$ 





### Field emission scanning microscope (FESM)



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### **Profilometer with AFM and SEM with EDX**

### Additional surface analysis of whole samples and relocalized areas of enhanced FE

Optical profilometer with lateral resolution of 2 µm and height resolution of 3 nm



combined with atomic force microscope AFM Scanning speed: (100×100) pixels in 1 min



Scanning electron microscope SEM (XL-30) with energy dispersive X-ray analysis EDX



CARE06, Frascati



### **Preparation techniques for Nb samples**

Nb samples prepared like cavities at DESY Buffered chem. BCP or electropolished EP and **high pressure rinsed HPR** with water mostly in single cells, few in 9-cell cavities





28 mm





# Dry ice cleaning of Nb samples (DIC)

Process developed at FH Stuttgart and adapted for cavities at DESY





# **Quality control scans of EP/HPR-Nb prepared in 9-cell cavity**

### Profiles of whole sample and central part of sample scanned area 20×20 mm<sup>2</sup> $5 \times 5 \text{ mm}^2$



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PID-regulated U(x,y) for 1 nA scanned area =  $7.5 \times 7.5$  mm<sup>2</sup> flat W-anode  $Ø_a$ = 100 µm anode voltage U = 4800 V electrode spacing  $\Delta z = 32 \ \mu m$ 



no emission @ 120MV/m 5 emitters @ 150MV/m best EP/HPR sample yet



### **Emitter distribution on single crystal Nb after BCP/HPR**

Alternative approach for mirror-like surfaces:large crystal Nb+BCP30µm/HPRPID-regulated voltage maps U(x,y) for 1 nAscanned area =  $7.5 \times 7.5 \text{ mm}^2$ flat W-anode  $Ø_a$  = 100 µmanode voltage U = 4800 Velectrode spacing  $\Delta z$  = 32 µm $\Delta z$  = 24 µm





no emission @ 120MV/m 2 emitters @ 150MV/m  $\Rightarrow$  best FE performance of all Nb samples yet

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### **Emitter statistics for various types of Nb samples**



Systematically reduced FE by EP+HPR, DIC and large crystal Nb BCP+HPR of large crystal Nb is probably sufficient

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### Locally measured I/V-curves and FN-Analysis of emitters



### Typical FN-plots of a stable activated deactivated emitter -8.5 -6.0--9.0 -7.0--9.5 -8.5 -8.0 In (I/E2) (23) 10.0° In (I/E2) -9.0--10.5-10.0 -11.0--11.5-10.5 -12.0 0.002 0.004 0.006 0.008 0.005 0.0075 0.01 0.0125 0.015 0.0025 0.002 0.004 0.006 0.008 0.01 (1/E) (1/E) (1/E)

 $\begin{array}{l} {\sf E}_{\rm on}(1~{\rm nA}) = 76.9~{\rm MV/m} \\ {\beta _ \uparrow } = 19.3 \quad {\sf S}_ \uparrow = 1 {\times 10^{-13}}\,{\rm m}^2 \\ {\beta _ \downarrow } = 17.9 \quad {\sf S}_ \downarrow = 5 {\times 10^{-13}}\,{\rm m}^2 \end{array}$ 

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 $\begin{array}{l} {\sf E}_{\rm on}(1~{\rm nA}) = 103.3~{\rm MV/m} \\ \beta_{\uparrow} = 17.4 ~~ {\sf S}_{\uparrow} = 1 \times 10^{-11}\,{\rm m}^2 \\ \beta_{\downarrow} = 31.2 ~~ {\sf S}_{\downarrow} = 3 \times 10^{-16}\,{\rm m}^2 \end{array}$ 

 $\begin{array}{l} \mathsf{E}_{on}(1 \text{ nA}) = 54.3 \text{ MV/m} \\ \beta_{\uparrow} = 67.4 \quad \mathsf{S}_{\uparrow} = 2 \times 10^{-17} \text{ m}^2 \\ \beta_{\downarrow} = 61.2 \quad \mathsf{S}_{\downarrow} = 1 \times 10^{-15} \text{ m}^2 \end{array}$ 

### After first processing, most emitters are stable up to 100 nA



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### **Current processing of instable emitters**



Fluctuations / oscillations most probably caused by adsorbates

# Understanding of instabilities and nature of emitters very difficult





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### **Typical protrusion emitters containing only Nb (+ O?)**



### E<sub>on</sub>(2nA) < 60 MV/m ~500 µm long scratch (mishandling of sample)





E<sub>on</sub>(2nA) = 90 MV/m ~5 μm long groove  $\beta$  = 71, S = 2.3·10<sup>-6</sup> μm<sup>2</sup>

E<sub>on</sub>(2nA) > 140 MV/m ~1 μm small defect  $\beta$  = 59, S = 7·10<sup>-8</sup> μm<sup>2</sup>





### **Typical particulate emitters containing impurities**



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### **Effect of DIC on particulate and protrusion emitters**



E<sub>on</sub>(1nA) = 77 MV/m S particulate removed by DIC





FE of protrusion much reduced by DIC



 $\Rightarrow \beta = h/r \sim w/r \\ S \sim r^2$ 

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### Effect of DIC on a flake-like emitter with exposed edge



emitter of ~ 20  $\mu$ m size destroyed by DIC remnants emitting at higher  $E_{on}$ !

EDX: no foreign element detected (probably oxide of Nb)



emitter	HPR	HPR+DIC
E <sub>on</sub> (MV/m)	54.3	62.8
β <sub>↑</sub>	67.4	35.4
$\beta_{\downarrow}$	51.2	38.0
$S_{\uparrow}(m^2)$	<b>2</b> × <b>10</b> <sup>-17</sup>	<b>8.3</b> × 10 <sup>-13</sup>
$S_{\downarrow}(m^2)$	<b>1.2</b> × 10 <sup>-15</sup>	<b>2.4</b> × 10 <sup>-13</sup>





### **Correlation between FE onset field and emitter size ?**

based on FE measurements and SEM analysis of 38 field emitters



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# **Conclusions and outlook !**

- <u>Standard EP+HPR Nb sample</u> provides good FE performance no field emission up to  $E_{on} = 120 \text{ MV/m} \Rightarrow E_{acc} = 60 \text{ MV/m}$
- Large Nb crystal BCP+HPR samples show best FE results
  ⇒ interesting alternative for cavity fabrication !
- Particulates and protrusions identified as relevant emitters
- DIC effectively removes particulates and weakens protrusions
- After first processing, most emitters are stable up to 100 nA
  - $\Rightarrow$  instabilities and nature of emitters challenging !
- Evidence for correlation between onset field and emitter size
  fast FE quality control on samples for XFEL !





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